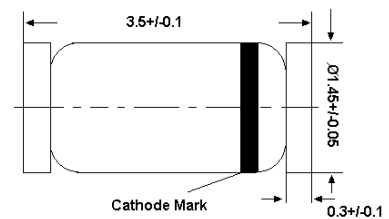


ST LL60P

Silicon Schottky Barrier Diode

Characteristics equivalent to or better than 1N60P
ideal for used in detection or for switching on the
radio, TV, etc.

LL-34



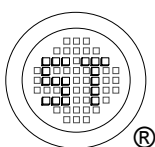
Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	20	V
Average Rectified Output Current	I_O	50	mA
Peak Forward Current	I_{FM}	150	mA
Surge Forward Current	I_{surge}	500	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

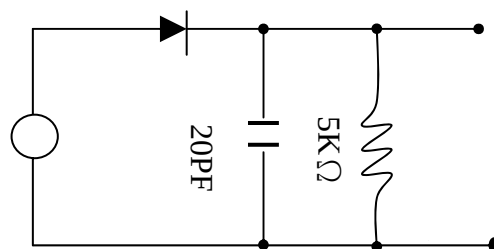
Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1\text{ V}$	I_F	4	-	mA
Reverse Current at $V_R = 10\text{ V}$	I_R	-	50	μA
Rectification efficiency at $V_i = 2\text{ Vrms}$, $R = 5\text{ K}\Omega$	η	55	-	%



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Dated: 21/09/2013 Rev: 02



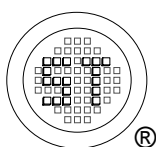
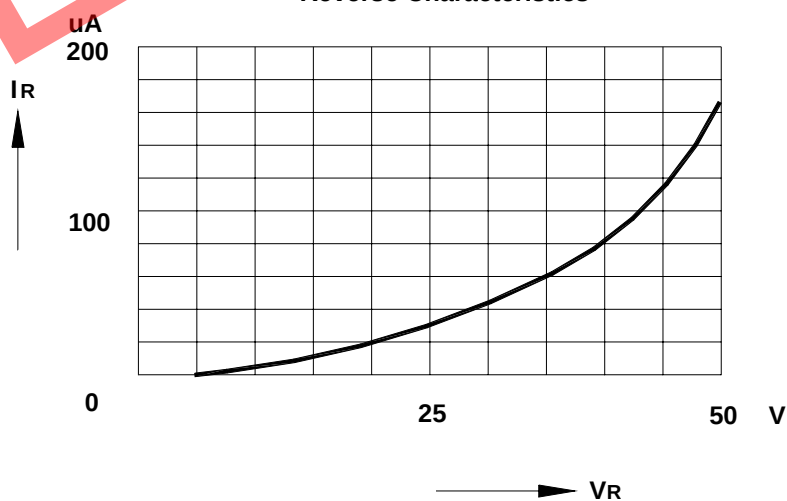
Input 2Vrms

Rectification Efficiency Measurement Circuit

Forward Characteristics



Reverse Characteristics



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